

**DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**
**Product Summary**

$BV_{DSS}$	$R_{DS(ON) \max}$	$I_D$ $T_A = +25^\circ\text{C}$
20V	0.55Ω @ $V_{GS} = 4.5\text{V}$	540mA

**Description and Applications**

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

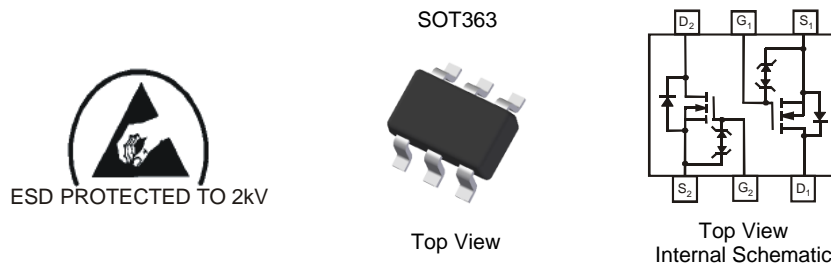
- Load Switch

**Features**

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMN2004DWKQ](#))**

**Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.006 grams (Approximate)


**Ordering Information (Note 4)**

Part Number	Case	Packaging
DMN2004DWK-7	SOT363	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**


NAB = Product Type Marking Code  
 YM = Date Code Marking  
 Y or Y = Year (ex: E = 2017)  
 M = Month (ex: 9 = September)

**Date Code Key**

Year	2006	2007	....	2013	2014	2015	2016	2017	2018	2019	2020	2021
Code	T	U	....	A	B	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	20	V
Gate-Source Voltage			$V_{GSS}$	$\pm 8$	V
Drain Current (Note 5)	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	540	mA
		$T_A = +85^\circ\text{C}$		390	
Pulsed Drain Current (Note 6)			$I_{DM}$	1.5	A

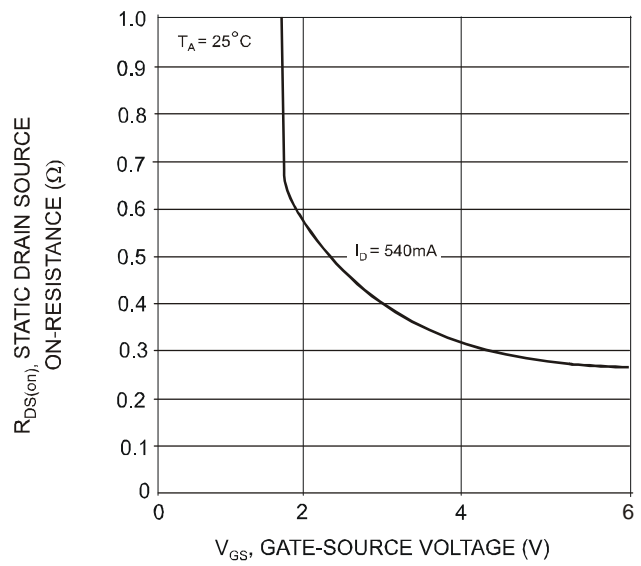
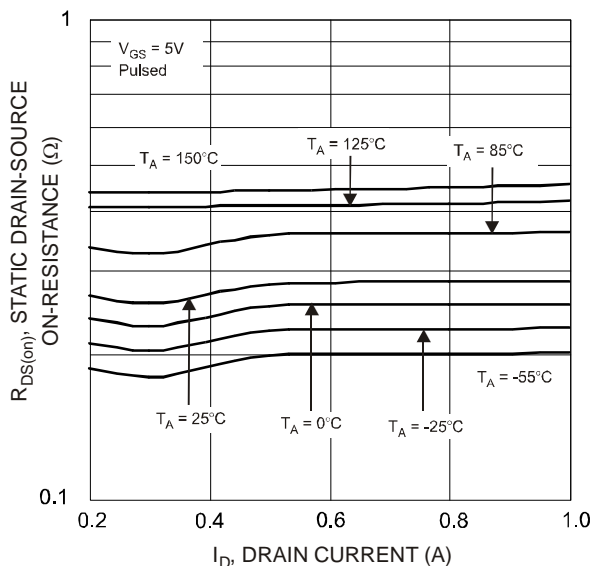
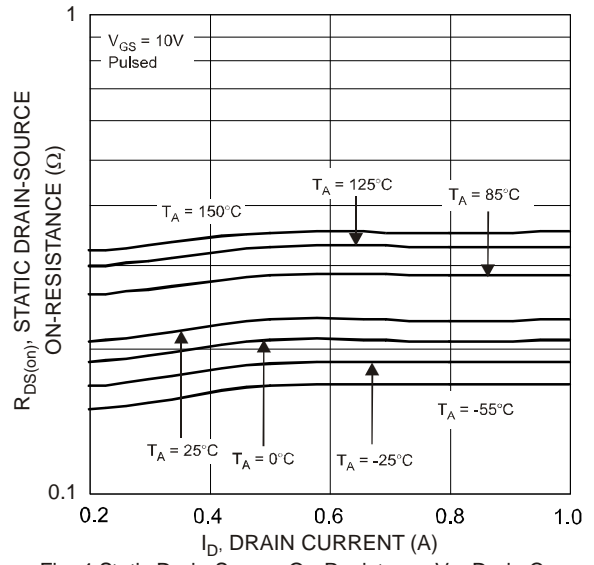
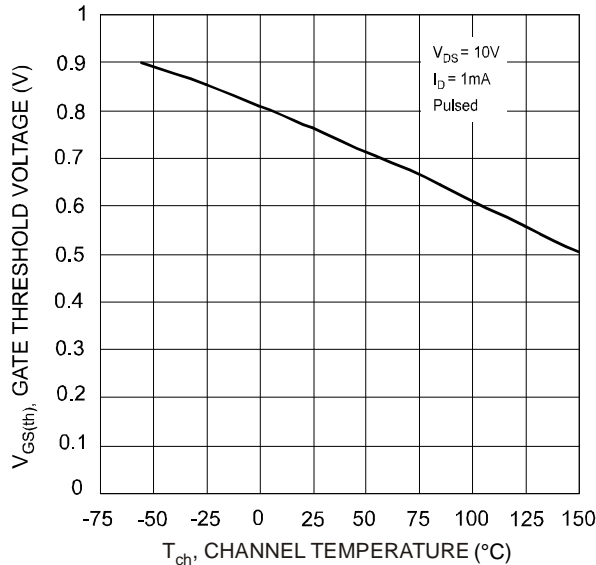
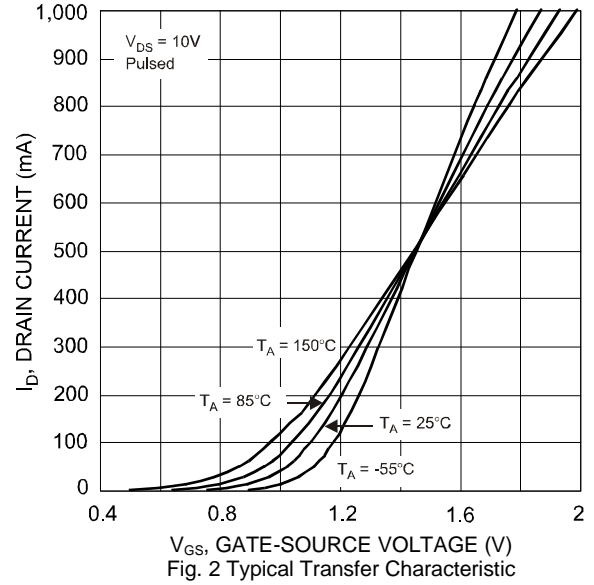
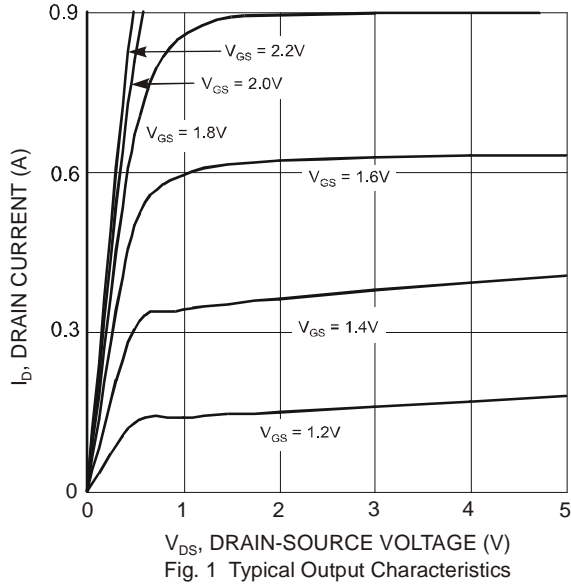
**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-65 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	20	—	—	V	$V_{GS} = 0\text{V}, I_D = 10\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 1$	$\mu\text{A}$	$V_{GS} = \pm 4.5\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.4	0.55	$\Omega$	$V_{GS} = 4.5\text{V}, I_D = 540\text{mA}$
			0.5	0.70		$V_{GS} = 2.5\text{V}, I_D = 500\text{mA}$
			0.7	0.9		$V_{GS} = 1.8\text{V}, I_D = 350\text{mA}$
Forward Transfer Admittance	$ Y_{fs} $	200	—	—	mS	$V_{DS} = 10\text{V}, I_D = 0.2\text{A}$
Diode Forward Voltage (Note 7)	$V_{SD}$	0.5	—	1.4	V	$V_{GS} = 0\text{V}, I_S = 115\text{mA}$
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	$C_{iss}$	—	36	150	pF	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	5.7	25	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	4.2	20	pF	
Total Gate Charge ( $V_{GS} = 4.5\text{V}$ )	$Q_g$	—	0.53	—	nC	$V_{DS} = 10\text{V}, I_D = 250\text{mA}$
Total Gate Charge ( $V_{GS} = 8.0\text{V}$ )	$Q_g$	—	0.95	—		
Gate-Source Charge	$Q_{gs}$	—	0.08	—		
Gate-Drain Charge	$Q_{gd}$	—	0.07	—		
Turn-On Delay Time	$t_{D(ON)}$	—	4.1	—	ns	$V_{DD} = 10\text{V}, R_L = 47\Omega,$ $V_{GEN} = 4.5\text{V}, R_{GEN} = 10\Omega$
Turn-On Rise Time	$t_r$	—	7.3	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	13.8	—	ns	
Turn-Off Fall Time	$t_f$	—	10.5	—	ns	

- Notes:
- Device mounted on FR-4 PCB.
  - Pulse width  $\leq 10\mu\text{s}$ , Duty Cycle  $\leq 1\%$ .
  - Short duration pulse test used to minimize self-heating effect.



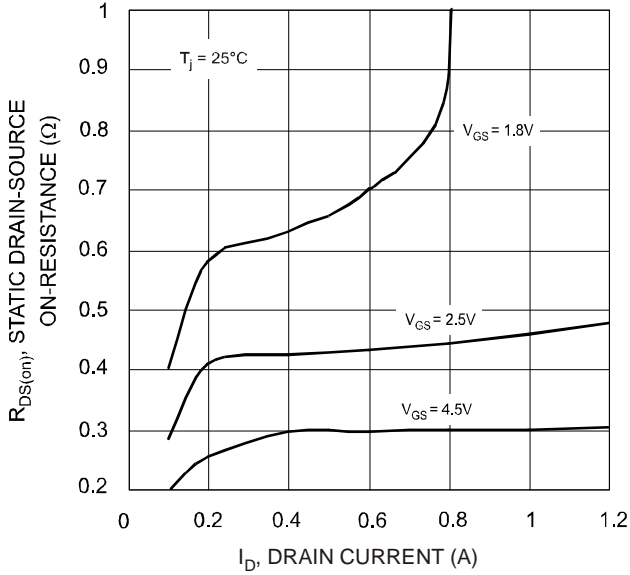


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage

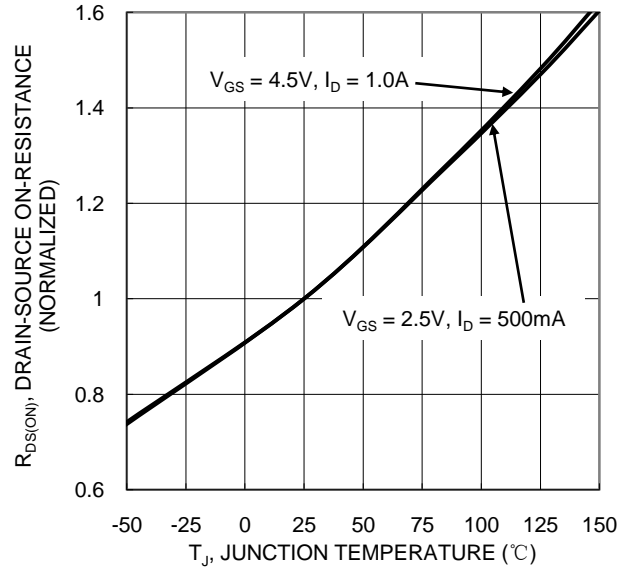


Fig. 8 On-Resistance Variation with Temperature

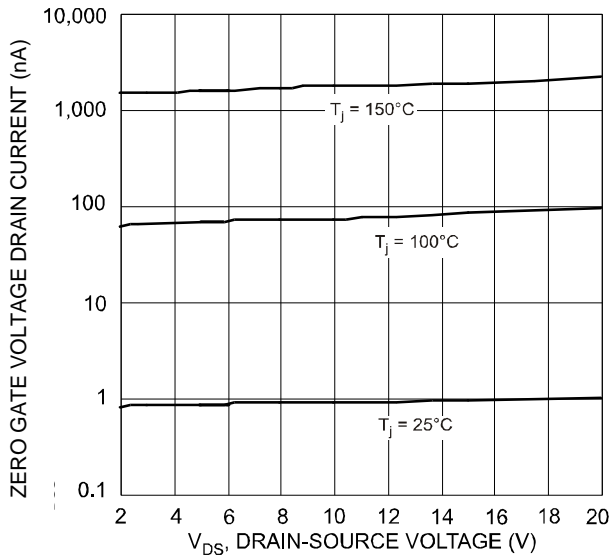


Fig. 9 Drain Source Leakage Current vs. Voltage

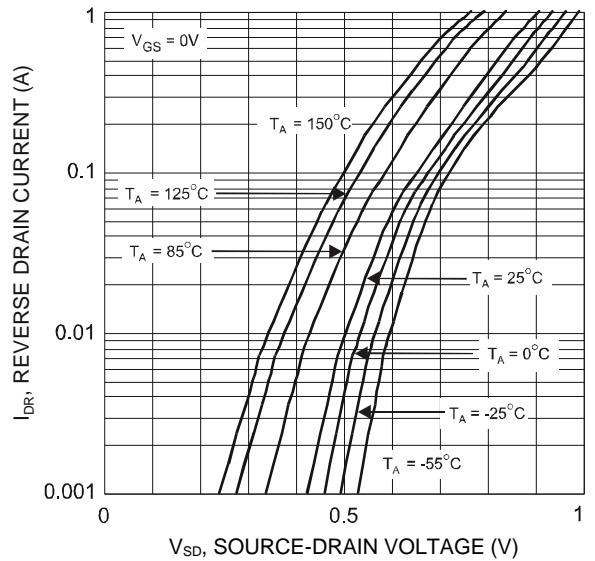


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage

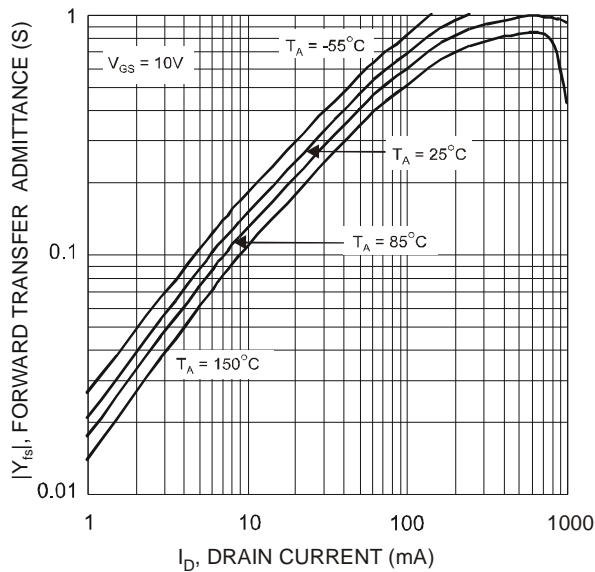


Fig. 11 Forward Transfer Admittance vs. Drain Current

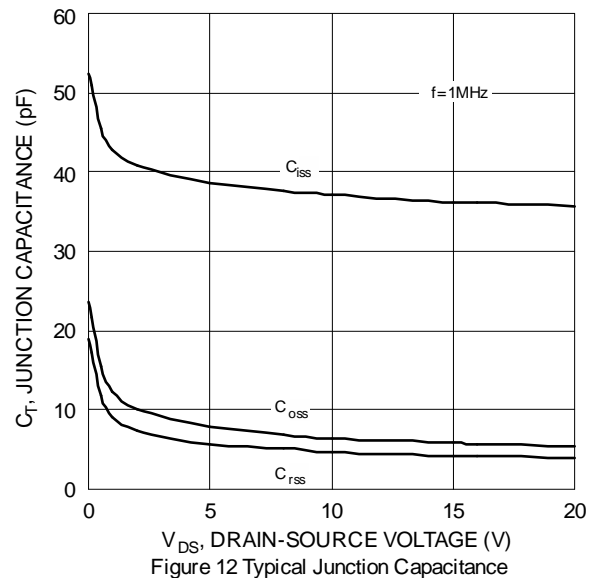


Figure 12 Typical Junction Capacitance

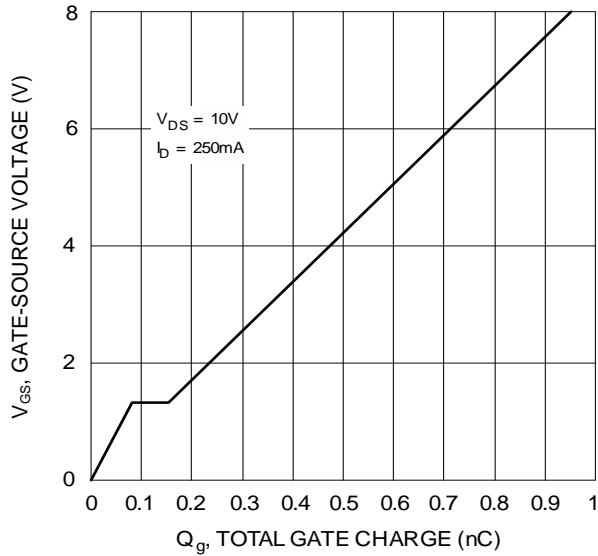


Figure 13 Gate Charge

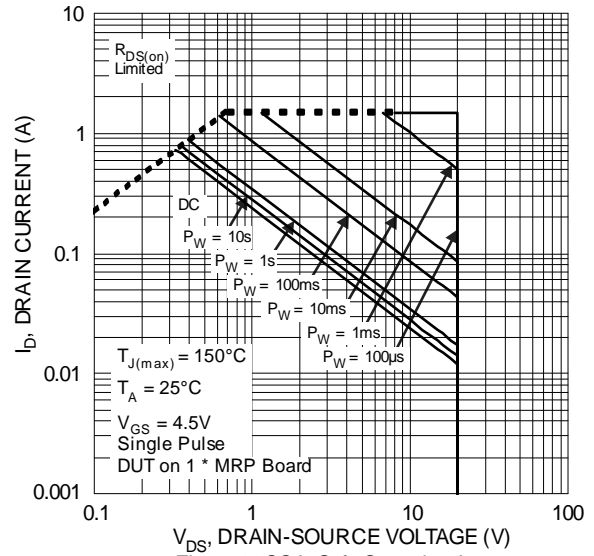
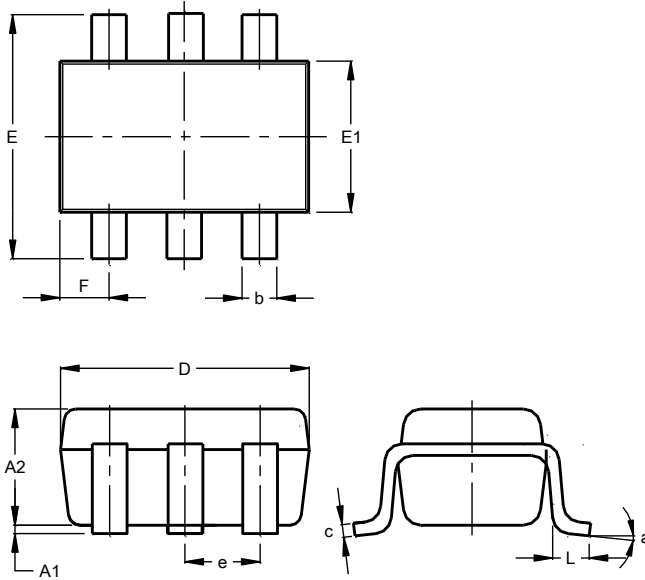


Figure 14 SOA, Safe Operation Area

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT363**

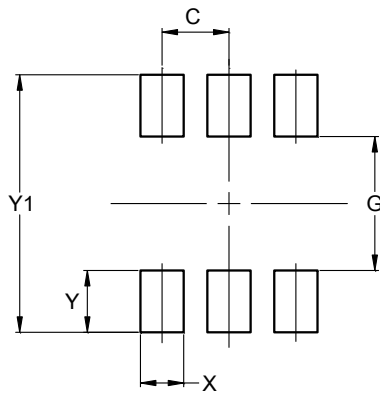


SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT363**



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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